

Title (en)
INTEGRATED ELECTRONIC CIRCUIT AND METHOD FOR PRODUCING THE SAME

Title (de)
INTEGRIERTE ELEKTRONISCHE SCHALTUNGSANORDNUNG UND VERFAHREN ZU IHRER HERSTELLUNG

Title (fr)
CIRCUIT ELECTRONIQUE INTEGRE ET SON PROCEDE DE PRODUCTION

Publication
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Application
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Abstract (en)
[origin: DE19810825A1] The integrated circuit has a semiconductor substrate (10), at least one inductance and at least one insulation region. The insulation region is formed from a porous semiconductor material (50). The insulation region extends deeper into the semiconductor substrate than the inductance. The porous semiconductor material and the semiconductor substrate preferably contain the same semiconductor elements. The porosity of the semiconductor material is preferably between 20 and 80 %. The material may be chemically transformed to improve its insulation properties. The material may e.g. be nitridised or oxidised.

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IPC 8 full level
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